

JFET Input Operational Amplifiers

These low cost JFET input operational amplifiers combine two state—of—the—art analog technologies on a single monolithic integrated circuit. Each internally compensated operational amplifier has well matched high voltage JFET input devices for low input offset voltage. The BIFET technology provides wide bandwidths and fast slew rates with low input bias currents, input offset currents, and supply currents.

The ON Semiconductor BIFET family offers single, dual and quad operational amplifiers which are pin–compatible with the industry standard MC1741, MC1458, and the MC3403/LM324 bipolar devices. The MC34001/ 34002/34004 series are specified from 0° to +70°C.

Input Offset Voltage Options of 5.0 mV and 10 mV Maximum

Low Input Bias Current: 40 pA
Low Input Offset Current: 10 pA
Wide Gain Bandwidth: 4.0 MHz

High Slew Rate: 13 V/μs

• Low Supply Current: 1.4 mA per Amplifier

• High Input Impedance: $10^{12} \Omega$

High Common Mode and Supply Voltage Rejection Ratios: 100 dB

Industry Standard Pinouts

MC34001, B MC34002, B MC34004, B

JFET INPUT OPERATIONAL AMPLIFIERS

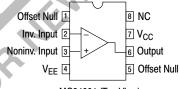




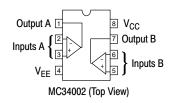
P SUFFIX PLASTIC PACKAGE CASE 626

D SUFFIX
PLASTIC PACKAGE
CASE 751
(SO-8)

PIN CONNECTIONS



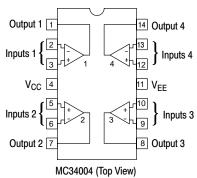
MC34001 (Top View)





P SUFFIX PLASTIC PACKAGE CASE 646

PIN CONNECTIONS



ORDERING INFORMATION

Op Amp Function	Device	Operating Temperature Range	Package
Cinala	MC34001BD, D	T 00 to 1 700C	SO-8
Single	MC34001BP, P	$T_A = 0^{\circ} \text{ to+ } 70^{\circ}\text{C}$	Plastic DIP
O	MC34002BD, D	T 00 to 17000	SO-8
Dual	MC34002BP, P	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP
Quad	MC34004BP, P	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V_{CC}, V_{EE}	±18	V
Differential Input Voltage (Note 1)	V _{ID}	±30	V
Input Voltage Range	V _{IDR}	±16	V
Open Short Circuit Duration	t _{SC}	Continuous	
Operating Ambient Temperature Range	T _A	0 to +70	°C
Operating Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

NOTES: 1. Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply.

ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R _S ≤ 10 k) MC3400XB MC3400X	V _{IO}	_	3.0 5.0	5.0 10	mV
Average Temperature Coefficient of Input Offset Voltage $R_S \le 10 \text{ k}$, $T_A = T_{low}$ to T_{high} (Note 2)	$\Delta V_{IO}/\Delta T$		10	_	μV/°C
Input Offset Current (V _{CM} = 0) (Note 3) MC3400XB MC3400X	I _{IO}	7	25 25	100 100	рА
Input Bias Current (V _{CM} = 0) (Note 3) MC3400XB MC3400X	I _{IB}	_	50 50	200 200	рА
Input Resistance	ri	_	10 ¹²	_	Ω
Common Mode Input Voltage Range	V _{ICR}	±11 —	+15 -12	_	V
Large Signal Voltage Gain ($V_O = \pm 10 \text{ V}$, $R_L = 2.0 \text{ k}$) MC3400XB MC3400X	A _{VOL}	50 25	150 100		V/mV
Output Voltage Swing $ (R_L \geq 10 \text{ k}) \\ (R_L \geq 2.0 \text{ k}) $	Vo	±12 ±10	±14 ±13		V
Common Mode Rejection Ratio (R _S ≤ 10 k) MC3400XB MC3400X	CMRR	80 70	100 100		dB
Supply Voltage Rejection Ratio (R _S ≤ 10 k) (Note 4) MC3400XB MC3400X	PSRR	80 70	100 100	_	dB
Supply Current (Each Amplifier) MC3400XB MC3400X	I _D	_	1.4 1.4	2.5 2.7	mA
Slew Rate ($A_V = 1.0$)	SR	_	13	_	V/μs
Gain-Bandwidth Product	GBW	_	4.0	_	MHz
Equivalent Input Noise Voltage $(R_S = 100 \Omega, f = 1000 Hz)$	e _n	_	25	_	nV/√Hz
Equivalent Input Noise Current (f = 1000 Hz)	i _n	_	0.01	_	pA/√Hz

NOTES: 2. T_{low} = 0°C for MC34001/34001B MC34002 MC34004/34004B T_{high} = +70°C for MC34001/34001B MC34002 MC34004/34004B

3. The input bias currents approximately double for every 10°C rise in junction temperature, T_J. Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

ELECTRICAL CHARACTERISTICS ($V_{CC} = +15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $T_A = T_{low}$ to T_{high} [Note 2].)

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{l} \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Input Offset Current ($V_{CM} = 0$) (Note 3$)} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Input Bias Current ($V_{CM} = 0$) (Note 3$)} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Common Mode Input Voltage Range} \\ \\ \text{Large Signal ($V_{O} = \pm 10 \text{ V}, R_{L} = 2.0 \text{ k}$)} \\ \text{MC3400XB} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Output Voltage Swing} \\ (R \geq 10 \text{ k}$) \\ \end{array}$	I _{IO}			4.0 4.0	1
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Offset Current ($V_{CM} = 0$) (Note 3) MC3400XB MC3400X Input Bias Current ($V_{CM} = 0$) (Note 3) MC3400XB MC3400X Common Mode Input Voltage Range Large Signal ($V_{O} = \pm 10 \text{ V}$, $R_{L} = 2.0 \text{ k}$) MC3400XB MC3400X Output Voltage Swing ($R \ge 10 \text{ k}$)	I _{IB}			4.0 4.0	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\label{eq:mc3400xB} \begin{split} &\text{MC3400X} \\ &\text{Input Bias Current (V}_{\text{CM}} = 0) \text{ (Note 3)} \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Common Mode Input Voltage Range} \\ &\text{Large Signal (V}_{\text{O}} = \pm 10 \text{ V, R}_{\text{L}} = 2.0 \text{ k)} \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Output Voltage Swing} \\ &\text{(R} \geq 10 \text{ k)} \end{split}$	I _{IB}	 ±11	_ 	4.0	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\label{eq:mc3400xB} \begin{split} &\text{MC3400X} \\ &\text{Common Mode Input Voltage Range} \\ &\text{Large Signal (V}_{\text{O}} = \pm 10 \text{ V}, \text{ R}_{\text{L}} = 2.0 \text{ k}) \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Output Voltage Swing} \\ &\text{(R} \geq 10 \text{ k}) \end{split}$	V _{ICR}	_ _ _ ±11		8.0	
	Large Signal ($V_O = \pm 10 \text{ V}$, $R_L = 2.0 \text{ k}$) MC3400XB MC3400X Output Voltage Swing ($R \ge 10 \text{ k}$)		±11			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	MC3400XB MC3400X Output Voltage Swing (R ≥ 10 k)	A _{VOL}		_	_	
$(R \geq 10 \text{ k}) \\ (R \geq 2.0 \text{ k}) \\ \\ \hline \\ Common Mode Rejection Ratio (R_S \leq 10 \text{ k}) \\ MC3400XB \\ MC3400X \\ \hline \\ MC3400X \\ \hline \\ MC3400X \\ \hline \\ MC3400XB \\ MC3400X \\ \hline \\ MC3400XB \\ \hline \\ MC3400X \\ \hline \\ MC340X \\ \hline \\ MC3$	(R ≥ 10 k)			_		ν
MC3400XB MC3400X Supply Voltage Rejection Ratio (R _S ≤ 10 k) (Note 4) MC3400XB MC3400X Supply Current (Each Amplifier) MC3400X Supply Current (Each Amplifier) MC3400XB MC3400X MC3400X NOTES: 2. T _{Iow} = 0°C for MC34001/34001B MC34002 MC34004/34004B 3. The input bias currents approximately double for every 10°C rise in junction temperature, T _J . Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum. 4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	(11 = 2.0 K)	Vo		_		
MC3400XB MC3400X Supply Current (Each Amplifier) MC3400XB MC3400X NOTES: 2. T _{low} = 0°C for MC34001/34001B MC34002 MC34004/34004B 3. The input bias currents approximately double for every 10°C rise in junction temperature, T _J . Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum. 4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	MC3400XB	CMRR		14	=	
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	4. Supply voltage rejection ratio is measured for both supply magnitudes increasing	ing or decreasing	g simultaneous	lly, in accordan	ice with comm	on pr

^{3.} The input bias currents approximately double for every 10°C rise in junction temperature, T_J. Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

^{4.} Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

Figure 1. Input Bias Current versus Temperature

Figure 2. Output Voltage Swing versus Frequency

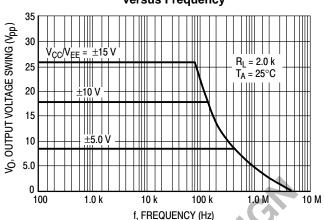


Figure 3. Output Voltage Swing versus Load Resistance

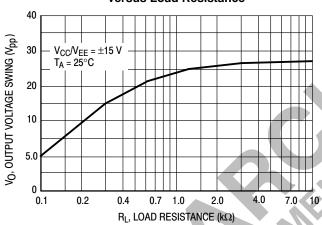


Figure 4. Output Voltage Swing versus Supply Voltage

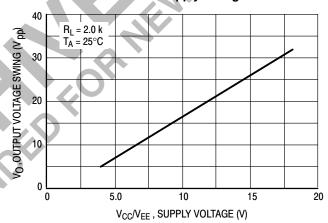


Figure 5. Output Voltage Swing versus Temperature

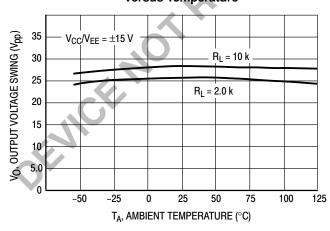


Figure 6. Supply Current per Amplifier versus Temperature

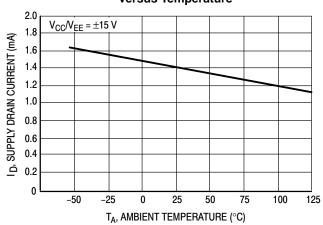


Figure 7. Large–Signal Voltage Gain and Phase Shift versus Frequency

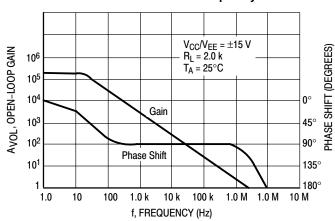


Figure 8. Large-Signal Voltage Gain versus Temperature

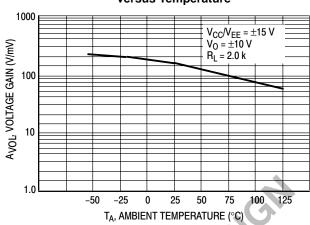


Figure 9. Normalized Slew Rate versus Temperature

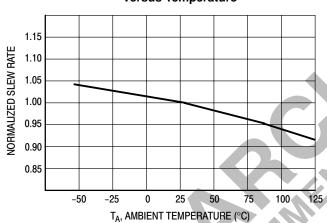


Figure 10. Equivalent Input Noise Voltage

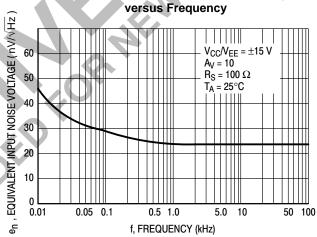
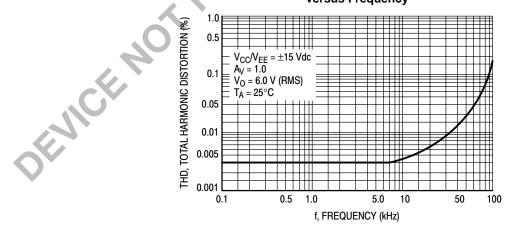


Figure 11. Total Harmonic Distortion versus Frequency



Representative Circuit Schematic (Each Amplifier)

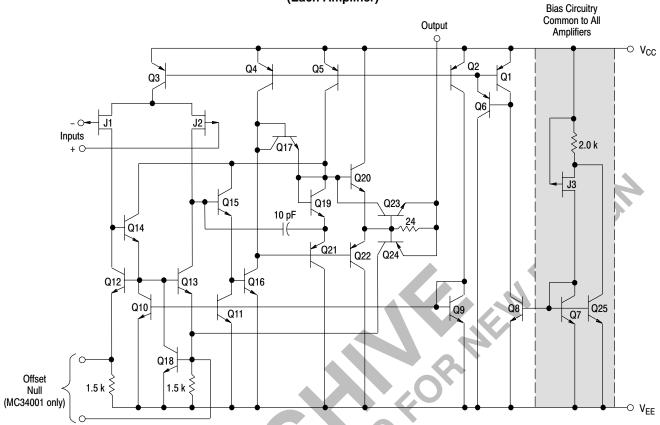
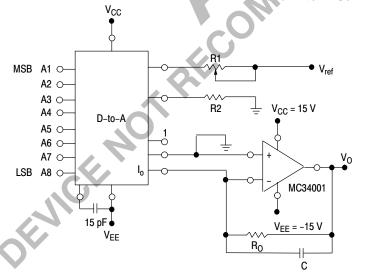


Figure 12. Output Current to Voltage Transformation for a D-to-A Converter



Settling time to within 1/2 LSB is approximately 4.0 μs from the time all bits are switched (C = 68 pF).

The value of C may be selected to minimize overshoot and ringing.

Theoretical V_O

$$V_{O} = \ \frac{V_{ref}}{R1} \ (R_{O}) \ \Big[\ \frac{A1}{2} \ + \frac{A2}{4} \ + \ \frac{A3}{8} \ + \frac{A4}{16} \ + \ \frac{A5}{32} \ + \ \frac{A6}{64} \ + \ \frac{A7}{128} \ + \frac{A8}{256} \ \Big]$$

Figure 13. Positive Peak Detector

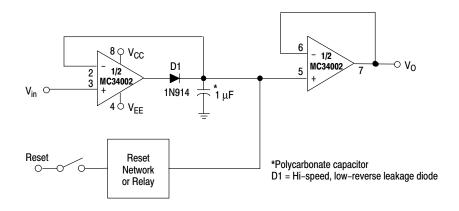
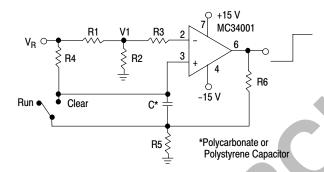


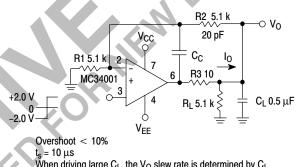
Figure 14. Long Interval RC Timer



Time (t) = R4 Cn (V_R/V_R-V_I) , $R_3 = R_4$, $R_5 = 0.1 R_6$ If R1 = R2: t = 0.693 R4C

Design Example: 100 Second Timer $V_R = 10 \text{ V}$ $C = 1.0 \,\mu\text{F}$ $R3 = R4 = 144 \,\text{M}$ R6 = 20 k R5 = 2.0 k R1 = R2 = 1.0 k

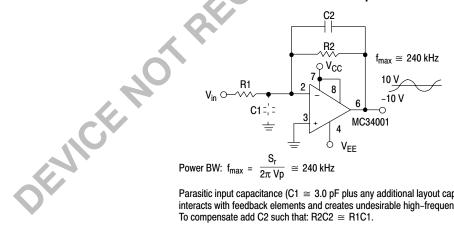
Figure 15. Isolating Large Capacitive Loads



 t_s = 10 μs When driving large C_L , the V_O slew rate is determined by C_L and I_{O(max)}:

$$\frac{\Delta V_0}{\Delta t} = \frac{I_0}{C_L} = \frac{0.02}{0.5} \quad \text{V/}\mu\text{s} = 0.04 \text{ V/}\mu\text{s} \text{ (with } C_L \text{ shown)}$$

Figure 16. Wide BW, Low Noise, **Low Drift Amplifier**

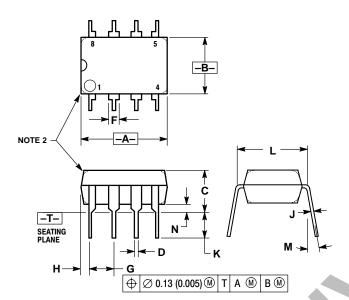


Parasitic input capacitance (C1 ≅ 3.0 pF plus any additional layout capacitance) interacts with feedback elements and creates undesirable high-frequency pole. To compensate add C2 such that: $R2C2 \cong R1C1$.

OUTLINE DIMENSIONS

P SUFFIX

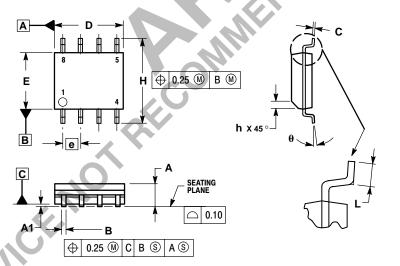
PLASTIC PACKAGE CASE 626-05 ISSUE K



- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62	BSC	0.300	BSC
M		10°	4	10°
N	0.76	1.01	0.030	0.040





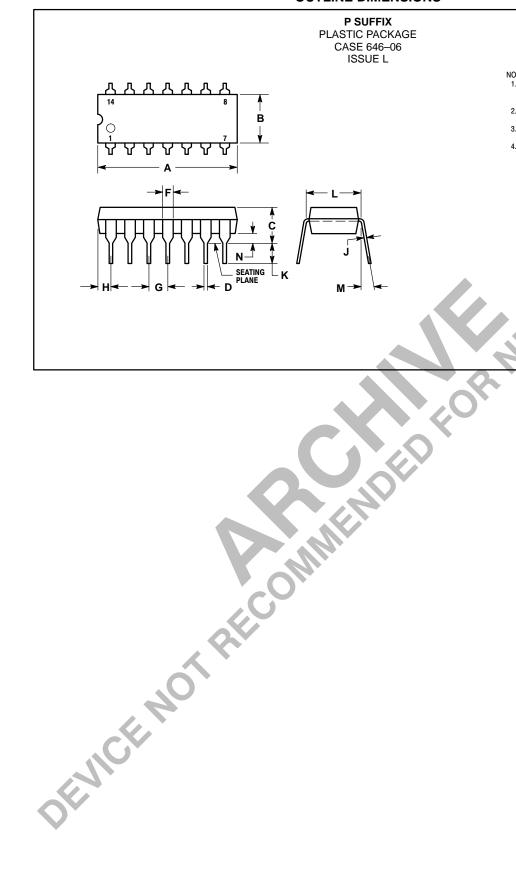
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. DIMENSIONS ARE IN MILLIMETERS.
 3. DIMENSION D AND E DO NOT INCLUDE MOLD
- MINENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR

PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
С	0.18	0.25		
D	4.80	5.00		
Е	3.80	4.00		
е	1.27	BSC		
Н	5.80	6.20		
h	0.25	0.50		
L	0.40	1.25		
θ	0 °	7 °		

OUTLINE DIMENSIONS



NOTES:

- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54	BSC
Н	0.052	0.095	1.32	2.41
L	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
٦	0.300 BSC		7.62	BSC
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01







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